

54ACT11000, 74ACT11000 QUADRUPLE 2-INPUT POSITIVE-NAND GATES

SCAS002A – D2957, JUNE 1987 – REVISED APRIL 1993

- Inputs Are TTL-Voltage Compatible
- Flow-Through Architecture Optimizes PCB Layout
- Center-Pin V_{CC} and GND Configurations Minimize High-Speed Switching Noise
- EPIC™ (Enhanced-Performance Implanted CMOS) 1- μ m Process
- 500-mA Typical Latch-Up Immunity at 125°C
- Package Options Include Plastic Small-Outline Packages, Ceramic Chip Carriers, and Standard Plastic and Ceramic 300-mil DIPs

description

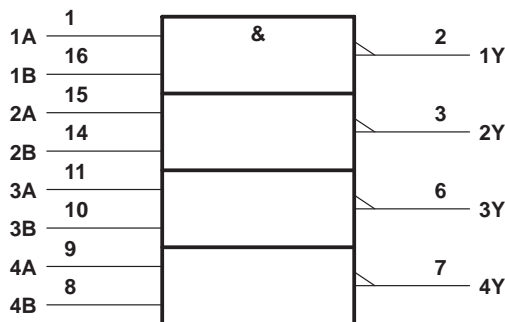
These devices contain four independent 2-input NAND gates. They perform the Boolean functions $Y = \overline{A \cdot B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

The 54ACT11000 is characterized for operation over the full military temperature range of -55°C to 125°C . The 74ACT11000 is characterized for operation from -40°C to 85°C .

FUNCTION TABLE
(each gate)

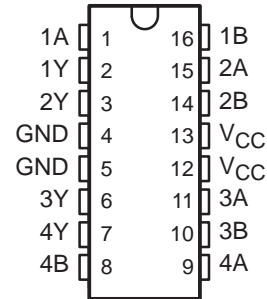
INPUTS		OUTPUT
A	B	Y
H	H	L
L	X	H
X	L	H

logic symbol†

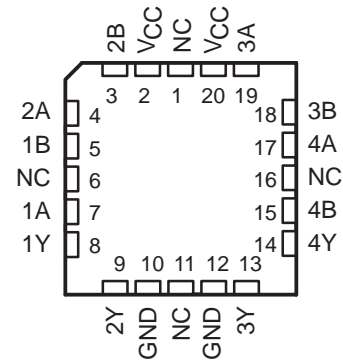


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, J, and N packages.

54ACT11000 . . . J PACKAGE
74ACT11000 . . . D OR N PACKAGE
(TOP VIEW)

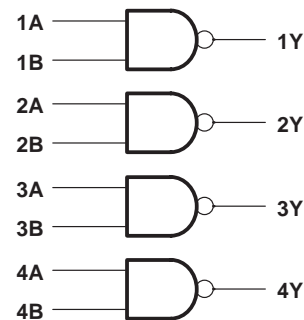


54ACT11000 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

logic diagram (positive logic)



EPIC is a trademark of Texas Instruments Incorporated.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

TEXAS
INSTRUMENTS

POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Copyright © 1993, Texas Instruments Incorporated

54ACT11000, 74ACT11000 QUADRUPLE 2-INPUT POSITIVE-NAND GATES

SCAS002A – D2957, JUNE 1987 – REVISED APRIL 1993

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	-0.5 V to 6 V
Input voltage range, V_I (see Note 1)	-0.5 V to $V_{CC} + 0.5$ V
Output voltage range, V_O (see Note 1)	-0.5 V to $V_{CC} + 0.5$ V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$)	± 20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$)	± 50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC})	± 50 mA
Continuous current through V_{CC} or GND	± 100 mA
Storage temperature range	-65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

recommended operating conditions

		54ACT11000		74ACT11000		UNIT
		MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	4.5	5.5	4.5	5.5	V
V_{IH}	High-level input voltage	2		2		V
V_{IL}	Low-level input voltage		0.8		0.8	V
V_I	Input voltage	0	V_{CC}	0	V_{CC}	V
V_O	Output voltage	0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current		-24		-24	mA
I_{OL}	Low-level output current		24		24	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	10	0	10	ns/V
T_A	Operating free-air temperature	-55	125	-40	85	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	$T_A = 25^\circ\text{C}$			54ACT11000		74ACT11000		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V_{OH}	$I_{OH} = -50 \mu\text{A}$	4.5 V	4.4			4.4		4.4	V	
		5.5 V	5.4			5.4		5.4		
	$I_{OH} = -24 \text{ mA}$	4.5 V	3.94			3.7		3.8		
		5.5 V	4.94			4.7		4.8		
		5.5 V				3.85				
	$I_{OH} = -75 \text{ mA}^\ddagger$	5.5 V					3.85			
V_{OL}	$I_{OL} = 50 \mu\text{A}$	4.5 V			0.1		0.1	0.1	V	
		5.5 V			0.1		0.1	0.1		
	$I_{OL} = 24 \text{ mA}$	4.5 V			0.36		0.5	0.44		
		5.5 V			0.36		0.5	0.44		
	$I_{OL} = 50 \text{ mA}^\ddagger$	5.5 V					1.65			
	$I_{OL} = 75 \text{ mA}^\ddagger$	5.5 V					1.65			
I_I	$V_I = V_{CC}$ or GND	5.5 V			± 0.1		± 1	± 1	μA	
I_{CC}	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			4		80	40	μA	
ΔI_{CC}^\S	One input at 3.4 V, Other inputs at GND or V_{CC}	5.5 V			0.9		1	1	mA	
C_i	$V_I = V_{CC}$ or GND	5 V		3.5					pF	

† Not more than one output should be tested at a time, and the duration of the test should not exceed 10 ms.

§ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or V_{CC} .



54ACT11000, 74ACT11000 QUADRUPLE 2-INPUT POSITIVE-NAND GATES

SCAS002A – D2957, JUNE 1987 – REVISED APRIL 1993

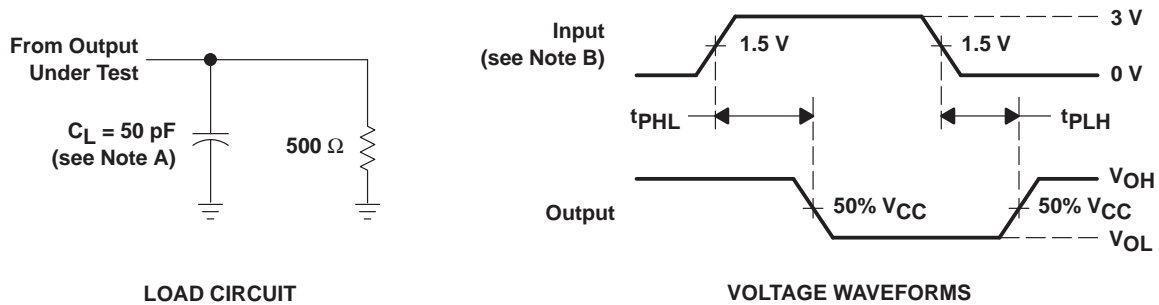
switching characteristics over recommended ranges of supply voltage and free-air temperature (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$T_A = 25^\circ\text{C}$			54ACT11000		74ACT11000		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A or B	Y	1.5	7.2	10.9	1.5	13.3	1.5	12.3	ns
t_{PHL}			1.5	5.8	8	1.5	9.5	1.5	8.8	

operating characteristics, $V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	TYP	UNIT
C_{pd} Power dissipation capacitance per gate	$C_L = 50\text{ pF}$, $f = 1\text{ MHz}$	23	pF

PARAMETER MEASUREMENT INFORMATION



- NOTES: A. C_L includes probe and jig capacitance.
 B. Input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r = 3\text{ ns}$, $t_f = 3\text{ ns}$.
 C. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74ACT11000DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74ACT11000DR	SOIC	D	16	2500	340.5	336.1	32.0

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (<https://www.ti.com/legal/termsofsale.html>) or other applicable terms available either on [ti.com](https://www.ti.com) or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2021, Texas Instruments Incorporated